

30V N-Channel NexFET™ Power MOSFET

 Check for Samples: [CSD17311Q5](#)

FEATURES

- Optimized for 5V Gate Drive
- Ultra Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm x 6-mm Plastic Package

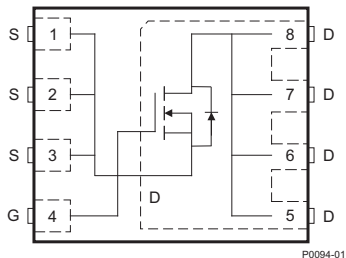
APPLICATIONS

- Notebook Point-of-Load
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems

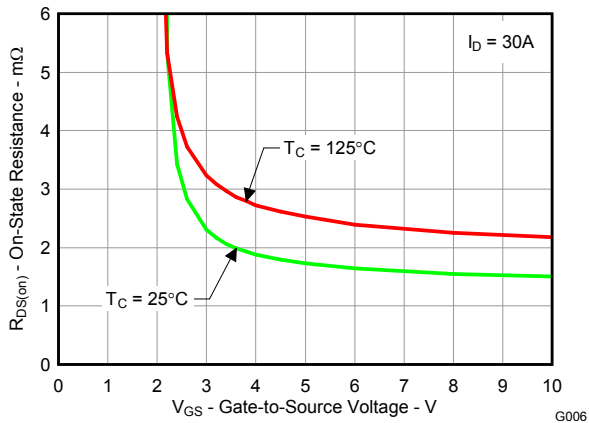
DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications, and optimized for 5V gate drive applications.

Top View



P0094-01

 $R_{DS(on)}$ vs V_{GS}


G006

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30	V
Q_g	Gate Charge Total (4.5V)	24	nC
Q_{gd}	Gate Charge Gate to Drain	5.2	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	2.3 mΩ
		$V_{GS} = 4.5V$	1.8 mΩ
		$V_{GS} = 8V$	1.6 mΩ
$V_{GS(th)}$	Threshold Voltage	1.2	V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17311Q5	SON 5-mm x 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

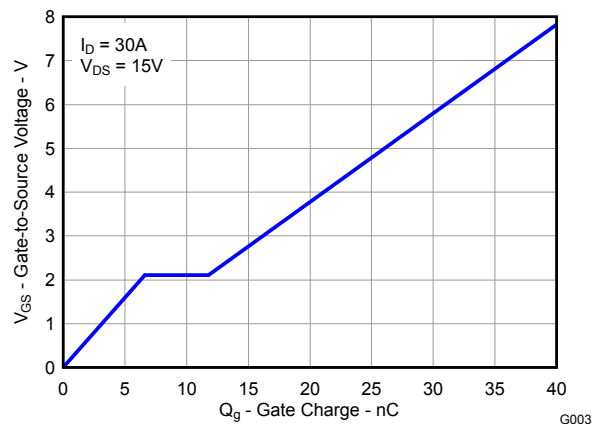
ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	100	A
	Continuous Drain Current ⁽¹⁾	32	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ⁽²⁾	200	A
P_D	Power Dissipation ⁽¹⁾	3.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Avalanche Energy, Single Pulse $I_D = 113A, L = 0.1mH, R_G = 25\Omega$	638	mJ

(1) Typical $R_{\theta JA} = 40^\circ\text{C}/\text{W}$ when mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

GATE CHARGE



G003



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

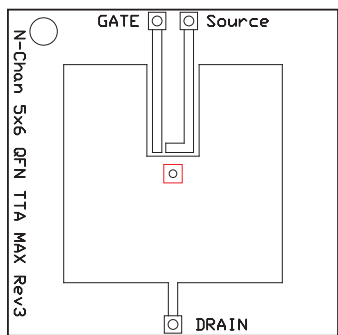
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	30			V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 24V$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.9	1.2	1.6	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V, I_D = 30A$		2.3	3.1	m Ω
		$V_{GS} = 4.5V, I_D = 30A$		1.8	2.3	m Ω
		$V_{GS} = 8V, I_D = 30A$		1.6	2	m Ω
g_{fs}	Transconductance	$V_{DS} = 15V, I_D = 30A$		200		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ $f = 1\text{MHz}$	3290	4280		pF
C_{oss}	Output Capacitance		1740	2260		pF
C_{rss}	Reverse Transfer Capacitance		85	110		pF
R_G	Series Gate Resistance		1.2	2.4		Ω
Q_g	Gate Charge Total (4.5V)	$V_{DS} = 15V,$ $I_{DS} = 30A$	24	31		nC
Q_{gd}	Gate Charge Gate to Drain		5.2			nC
Q_{gs}	Gate Charge Gate to Source		6.6			nC
$Q_{g(th)}$	Gate Charge at V_{th}		3.9			nC
Q_{oss}	Output Charge	$V_{DS} = 14.8V, V_{GS} = 0V$	47			nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 15V, V_{GS} = 4.5V,$ $I_{DS} = 30A, R_G = 2\Omega$	12			ns
t_r	Rise Time		18			ns
$t_{d(off)}$	Turn Off Delay Time		33			ns
t_f	Fall Time		12			ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_{SD} = 30A, V_{GS} = 0V$	0.85	1		V
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 14.8V, I_F = 30A,$ $di/dt = 300A/\mu\text{s}$	74			nC
t_{rr}	Reverse Recovery Time		39			ns

THERMAL CHARACTERISTICS

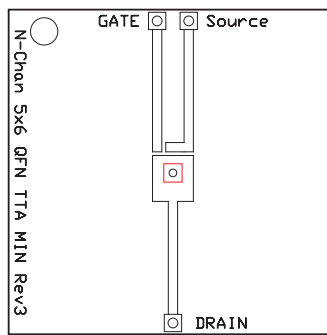
($T_A = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			49	$^\circ\text{C/W}$

- (1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 49^{\circ}\text{C/W}$
 when mounted on
 1 inch² (6.45 cm²) of
 2-oz. (0.071-mm thick)
 Cu.



Max $R_{\theta JA} = 120^{\circ}\text{C/W}$
 when mounted on a
 minimum pad area of
 2-oz. (0.071-mm thick)
 Cu.

TYPICAL MOSFET CHARACTERISTICS

$T_A = 25^{\circ}\text{C}$, unless otherwise specified

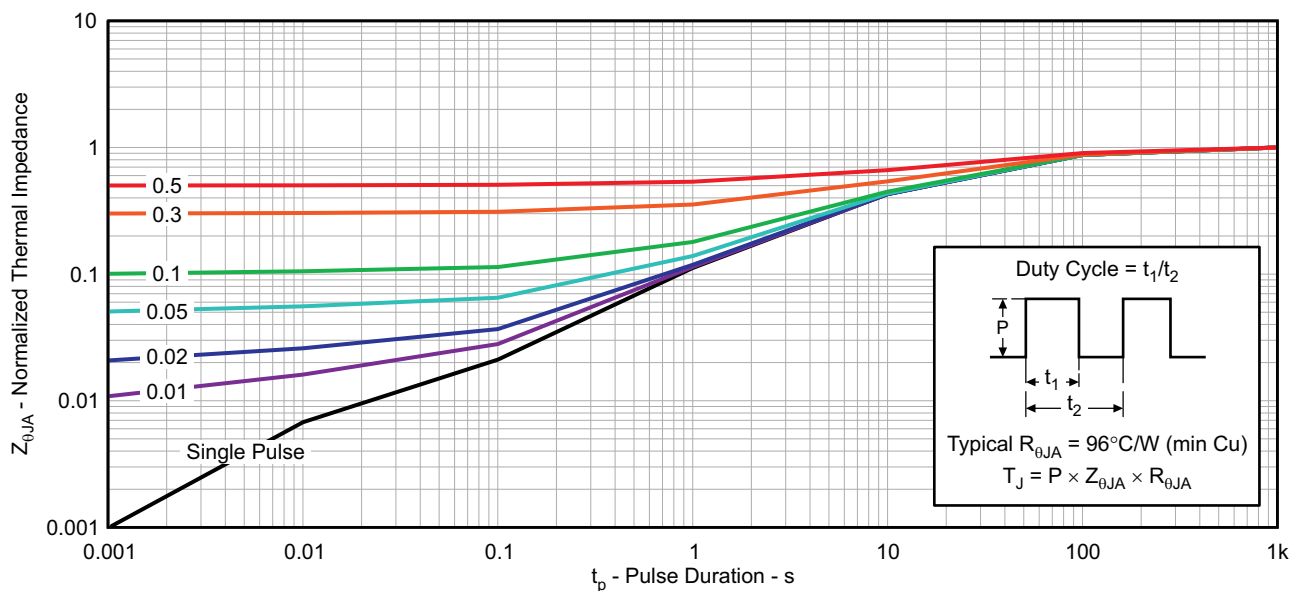


Figure 1. Transient Thermal Impedance

G012

TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

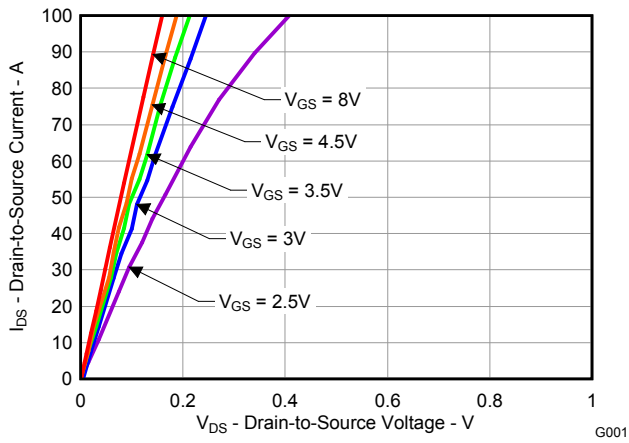


Figure 2. Saturation Characteristics

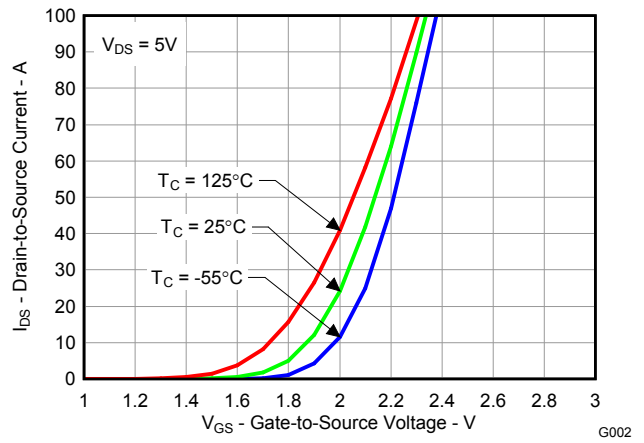


Figure 3. Transfer Characteristics

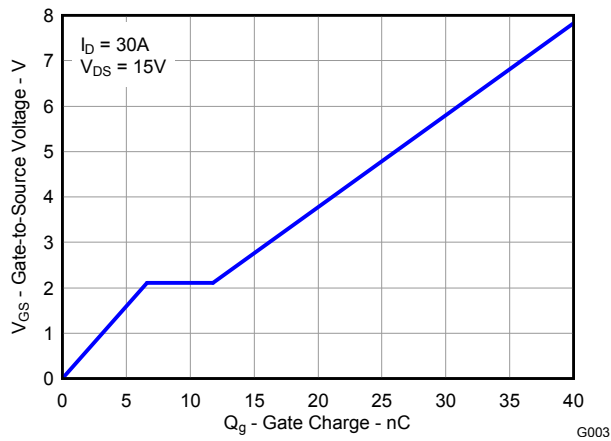


Figure 4. Gate Charge

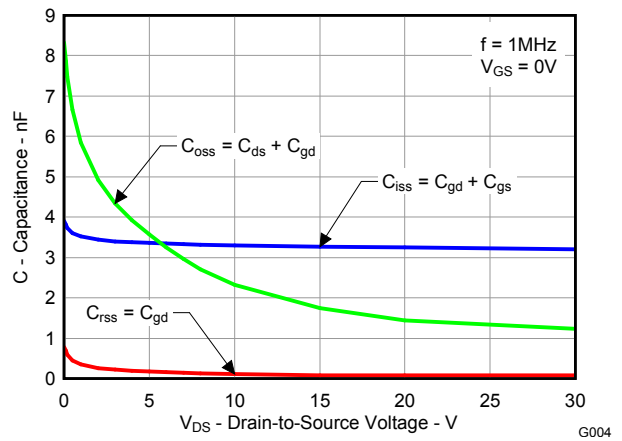


Figure 5. Capacitance

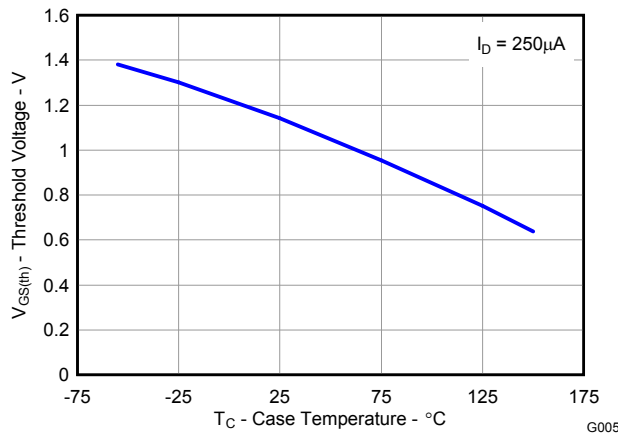


Figure 6. Threshold Voltage vs. Temperature

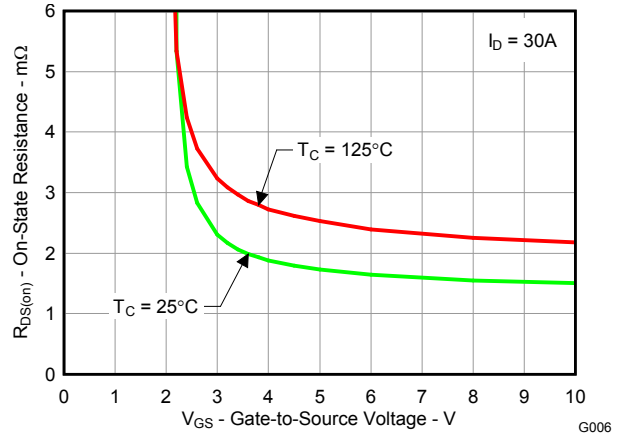


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

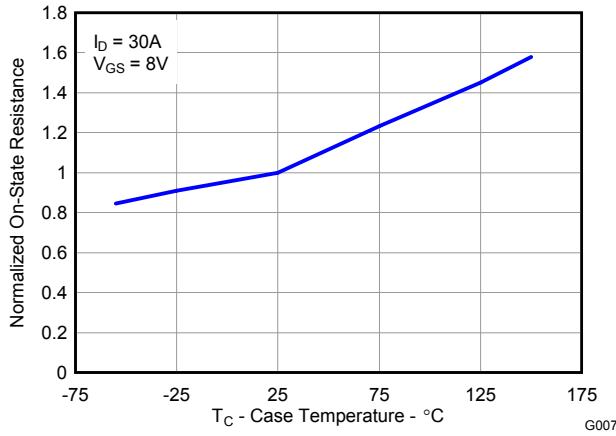


Figure 8. Normalized On-State Resistance vs. Temperature

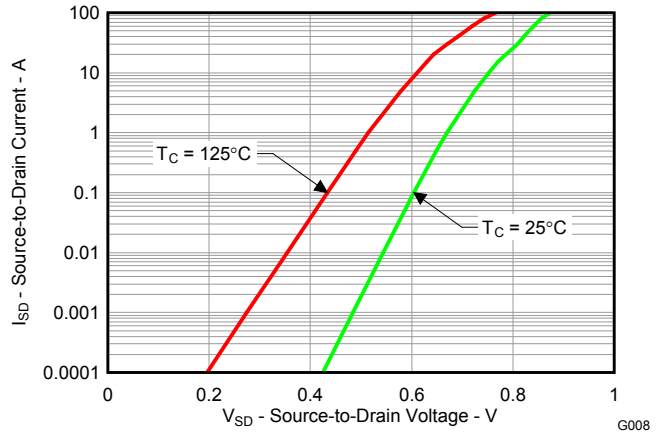


Figure 9. Typical Diode Forward Voltage

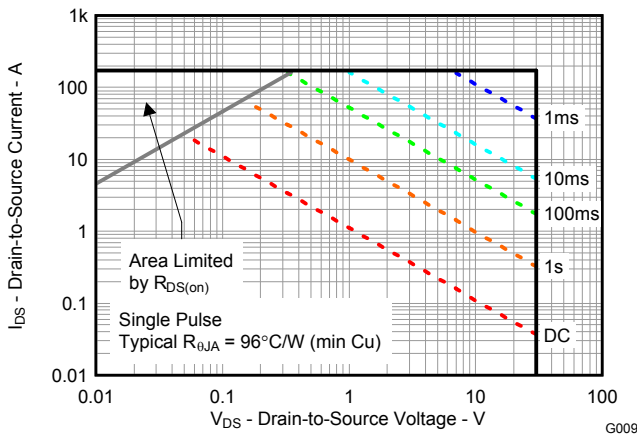


Figure 10. Maximum Safe Operating Area

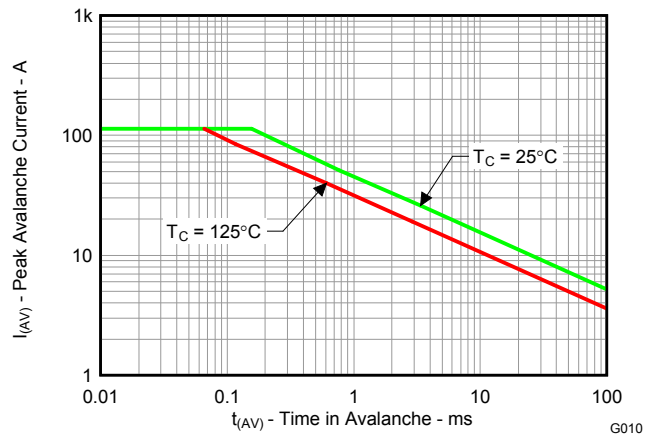


Figure 11. Single Pulse Unclamped Inductive Switching

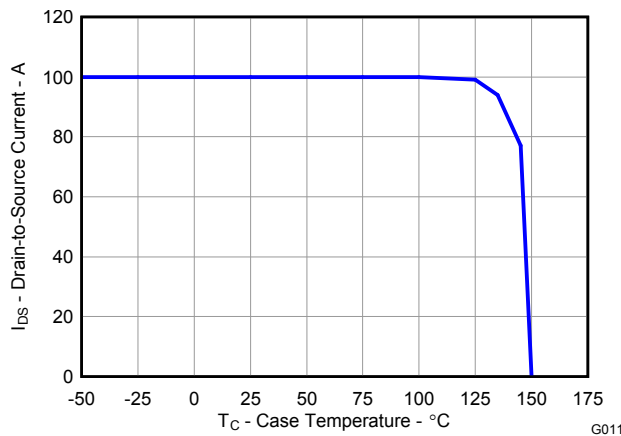
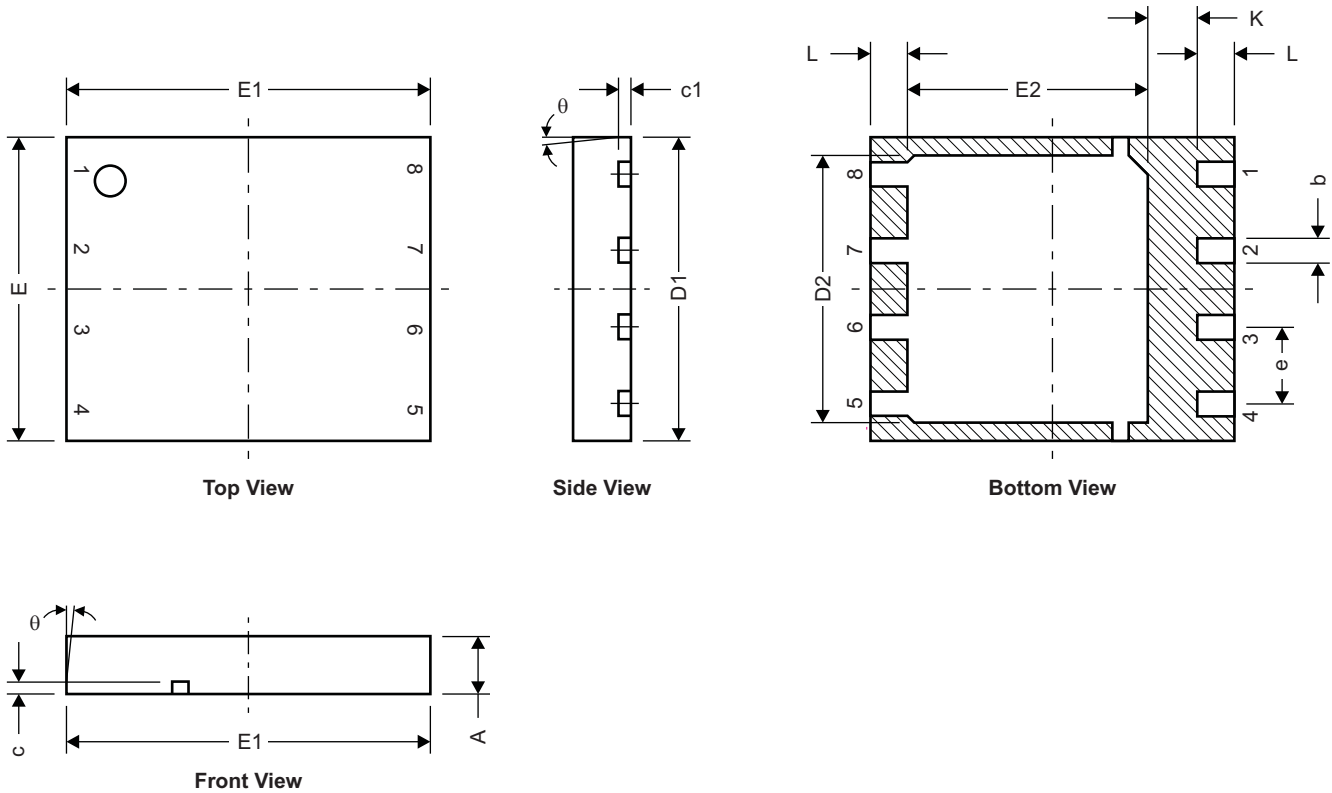


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

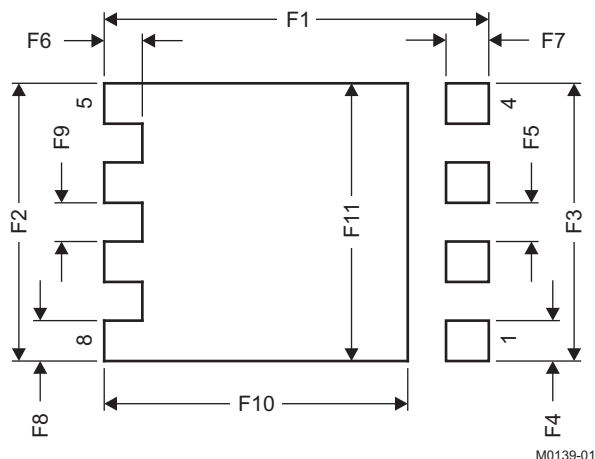
Q5 Package Dimensions



M0140-01

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

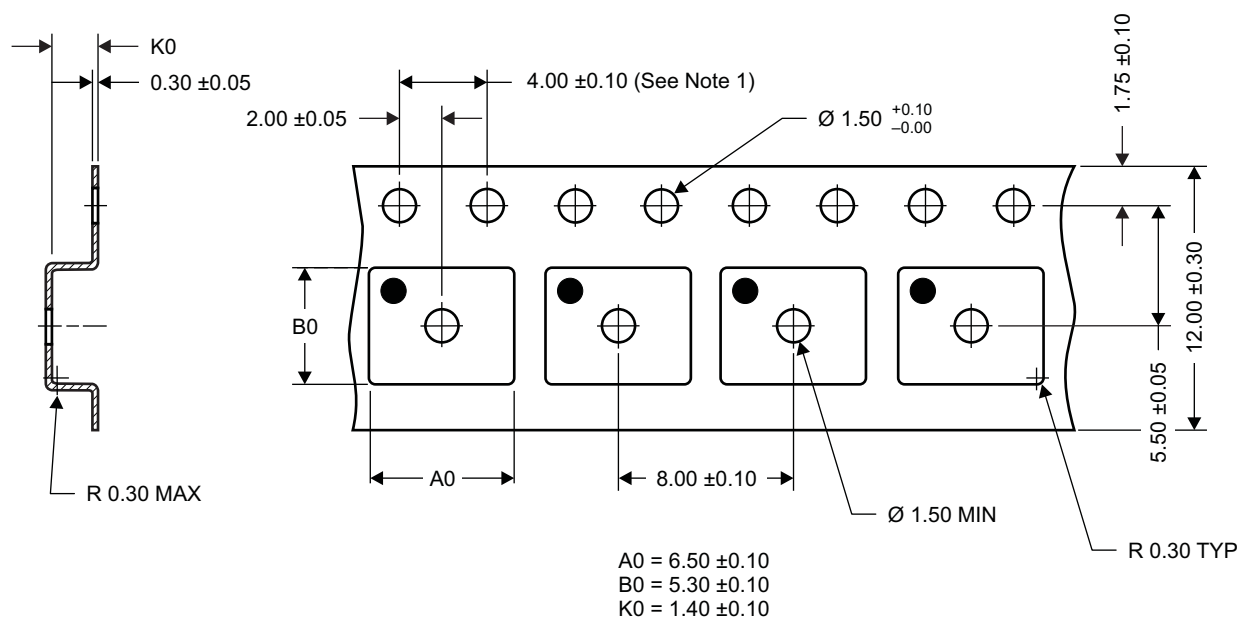
Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

Q5 Tape and Reel Information



- Notes:
- 10-sprocket hole-pitch cumulative tolerance ± 0.2
 - Camber not to exceed 1mm in 100mm, noncumulative over 250mm
 - Material: black static-dissipative polystyrene
 - All dimensions are in mm (unless otherwise specified)
 - Thickness: 0.30 ± 0.05 mm
 - MSL1 260°C (IR and convection) PbF reflow compatible

M0138-01

Package Marking Information

Location

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

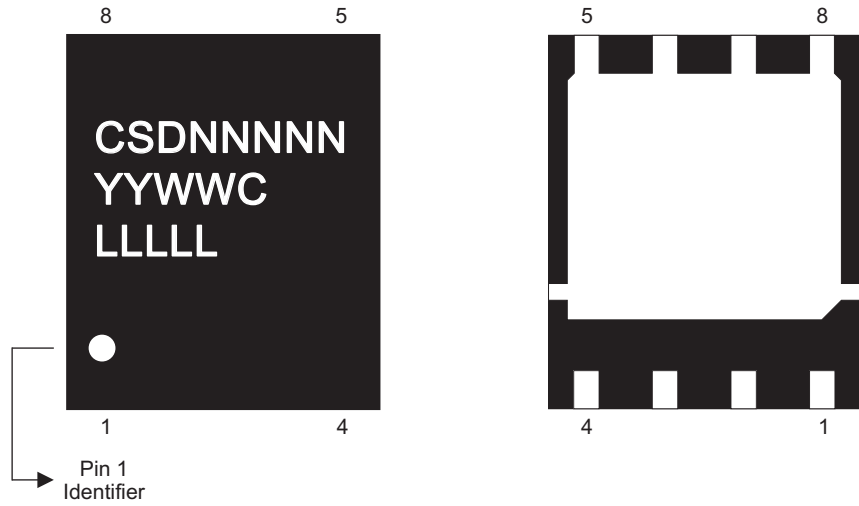
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLL = Last 5 digits of the Wafer Lot #



M0141-01

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
CSD17311Q5	PREVIEW	SON	DQH	8	2500	TBD	Call TI	Call TI	Samples Not Available

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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